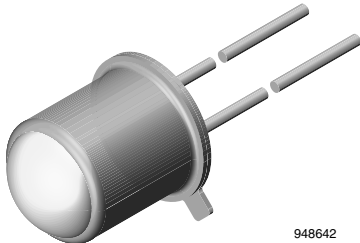


Infrared Emitting Diode, RoHS Compliant, 875 nm, GaAlAs



FEATURES

- Package type: leaded
- Package form: TO-18
- Dimensions (in mm): $\varnothing$ 4.7
- Peak wavelength: $\lambda_p = 875$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 12^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

DESCRIPTION

TSTA7300 is an infrared, 875 nm emitting diode in GaAlAs technology in a hermetically sealed TO-18 package with lens.

APPLICATIONS

- Radiation source near infrared range

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSTA7300	20	± 12	875	600

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSTA7300	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p \leq 100$ μ s	I_{FM}	200	mA
Surge forward current	$t_p \leq 100$ μ s	I_{FSM}	2.5	A
Power dissipation		P_V	180	mW
	$T_{case} \leq 25$ $^\circ$ C	P_V	500	mW
Junction temperature		T_j	100	$^\circ$ C
Storage temperature range		T_{stg}	- 55 to + 100	$^\circ$ C
Thermal resistance junction/ambient	leads not soldered	R_{thJA}	450	K/W
Thermal resistance junction/case	leads not soldered	R_{thJC}	150	K/W

Note

$T_{amb} = 25$ $^\circ$ C, unless otherwise specified



Infrared Emitting Diode, RoHS Compliant, Vishay Semiconductors 875 nm, GaAlAs

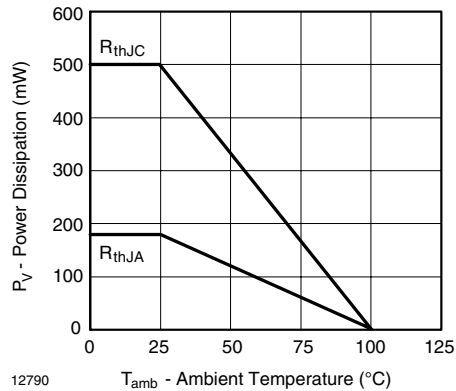


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

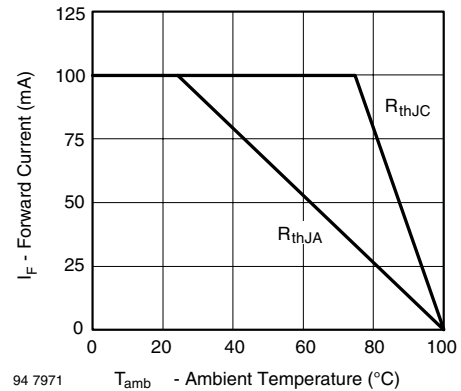


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}$, $t_p \leq 20 \text{ ms}$	V_F		1.4	1.8	V
Breakdown voltage	$I_R = 100 \text{ }\mu\text{A}$	$V_{(BR)}$	5			V
Junction capacitance	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, $E = 0$	C_j		20		pF
Radiant intensity	$I_F = 100 \text{ mA}$, $t_p \leq 20 \text{ ms}$	I_e	10	20	50	mW/sr
Radiant power	$I_F = 100 \text{ mA}$, $t_p \leq 20 \text{ ms}$	ϕ_e		10		mW
Temperature coefficient of ϕ_e	$I_F = 100 \text{ mA}$	$TK\phi_e$		- 0.7		%/K
Angle of half intensity		ϕ		± 12		deg
Peak wavelength	$I_F = 100 \text{ mA}$	λ_p		875		nm
Spectral bandwidth	$I_F = 100 \text{ mA}$	$\Delta\lambda$		80		nm
Rise time	$I_F = 100 \text{ mA}$	t_r		600		ns
	$I_F = 1.5 \text{ A}$, $t_p/T = 0.01$, $t_p \leq 10 \text{ }\mu\text{s}$	t_r		300		ns
Virtual source diameter		d		1		mm

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

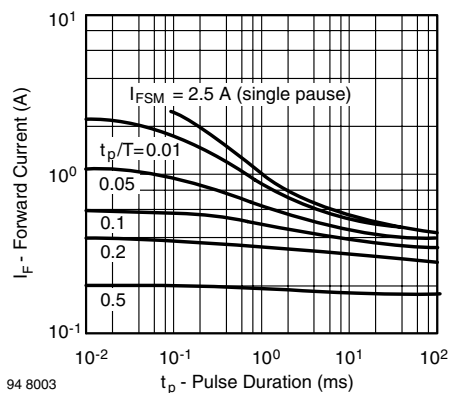


Fig. 3 - Pulse Forward Current vs. Pulse Duration

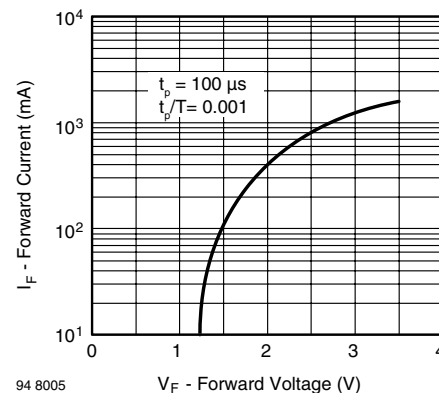


Fig. 4 - Forward Current vs. Forward Voltage

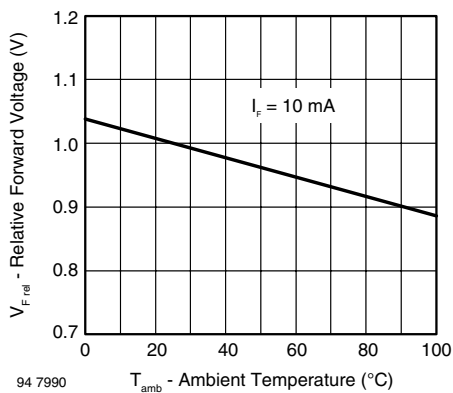


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

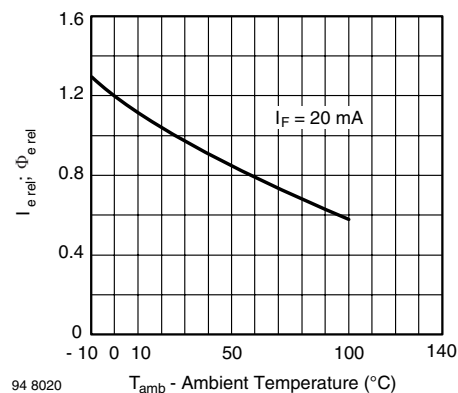


Fig. 8 - Rel. Radiant Intensity/Power vs. Ambient Temperature

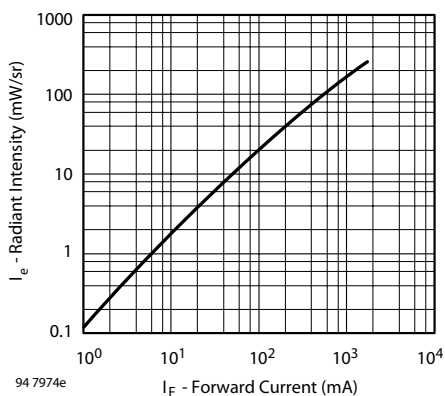


Fig. 6 - Radiant Intensity vs. Forward Current

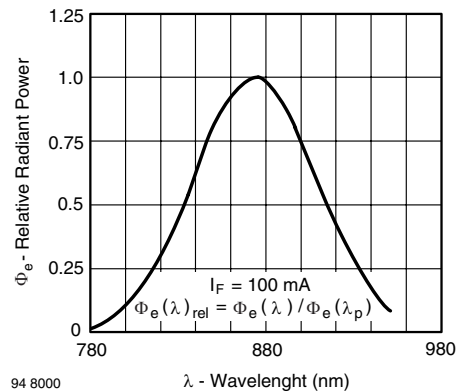


Fig. 9 - Relative Radiant Power vs. Wavelength

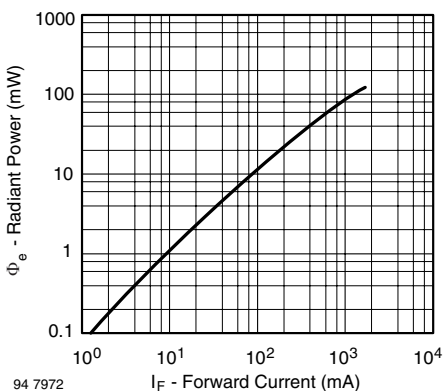


Fig. 7 - Radiant Power vs. Forward Current

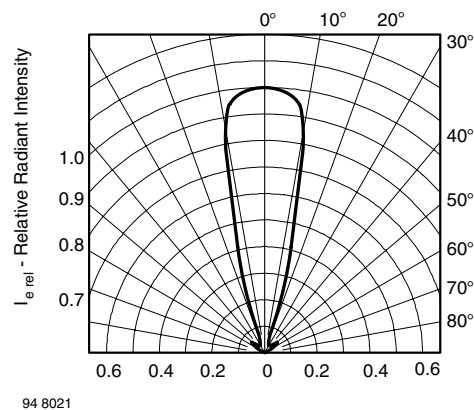
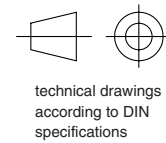
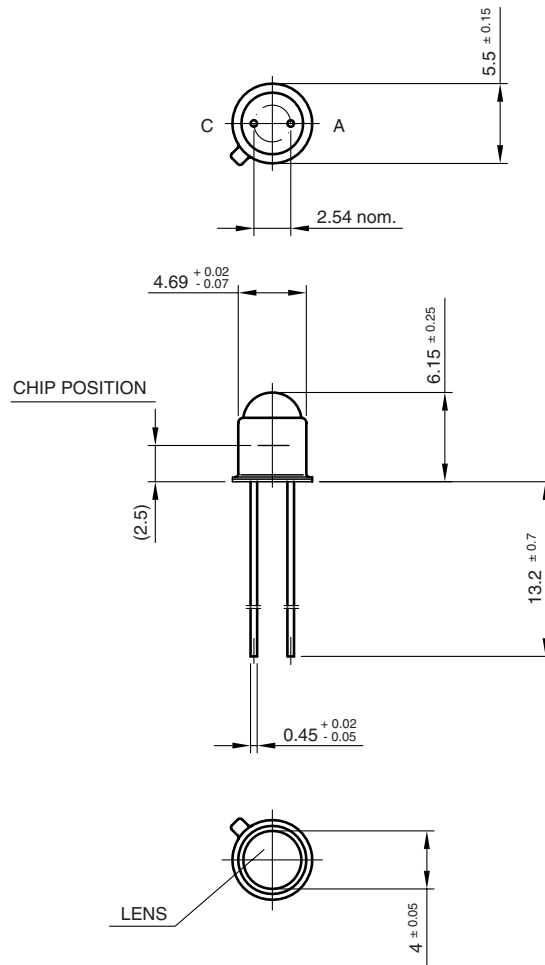


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

**PACKAGE DIMENSIONS** in millimeters

Drawing-No.: 6.503-5022.01-4
Issue: 2; 24.08.98
96 12179



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